



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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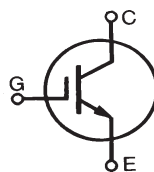


HiPerFAST™ IGBT

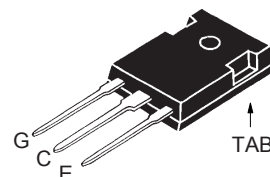
Short Circuit SOA Capability

IXSH24N60
IXSH24N60A

V_{CES}	I_{C90}	$V_{CE(sat)}$
600V	24A	2.2V
600V	24A	2.7V



TO-247 (IXSH)



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1\text{M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	48	A
I_{C90}	$T_C = 90^\circ\text{C}$	24	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	96	A
SSOA	$V_{GE} = 15\text{V}, T_J = 125^\circ\text{C}, R_G = 10\Omega$	$I_{CM} = 48$	A
(RBSOA)	Clamped inductive load	$@0.8 \cdot V_{CES}$	V
t_{SC}	$V_{GE} = 15\text{V}, V_{CE} = 360\text{V}, T_J = 125^\circ\text{C}$	10	μs
(SCSOA)	$R_G = 82\Omega$, non repetitive		
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13 / 10	Nm/lb.in.
T_L	Maximum lead temperature for soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6mm (0.062 in.) from case for 10s	260	$^\circ\text{C}$
Weight		6	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	600		V
$V_{GE(th)}$	$I_C = 1.5\text{mA}, V_{CE} = V_{GE}$	4.0		7.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{V}$ $T_J = 125^\circ\text{C}$			200 μA 1 mA
I_{GES}	$V_{CE} = 0\text{V}, V_{GE} = \pm 20\text{V}$			± 100 nA
$V_{CE(sat)}$	$I_C = 24\text{A}, V_{GE} = 15\text{V}, \text{Note 1}$	IXSH24N60 IXSH24N60A		2.2 V 2.7 V

Features

- International standard package JEDEC TO-247AD
- High frequency IGBT with guaranteed Short Circuit SOA Capability
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$ - for low on-state conduction losses
- MOS Gate turn-on - drive simplicity

Applications

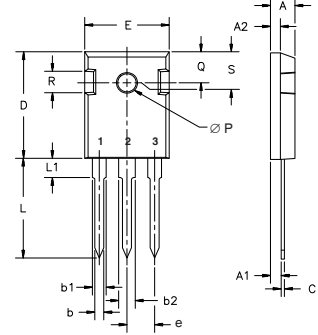
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Welding

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Switching speed for high frequency applications
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 24\text{A}$, $V_{CE} = 10\text{V}$, Note 1	9	23	S
$I_{C(ON)}$	$V_{GE} = 15\text{V}$, $V_{CE} = 10\text{V}$		65	A
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		1800	pF
C_{oes}			160	pF
C_{res}			45	pF
Q_g	$I_C = 24\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		75	nC
Q_{ge}			20	nC
Q_{gc}			35	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 24\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}$, $R_G = 10\Omega$		100	ns
t_{ri}			200	ns
$t_{d(off)}$			450	ns
t_{fi}		IXSH24N60	500	ns
E_{off}		IXSH24N60A	275	ns
		IXSH24N60A	2.0	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 24\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}$, $R_G = 10\Omega$		100	ns
t_{ri}			200	ns
E_{on}			1.2	mJ
$t_{d(off)}$			475	ns
		IXSH24N60	600	ns
		IXSH24N60A	450	ns
t_{fi}		IXSH24N60	4.0	mJ
E_{off}		IXSH24N60A	3.0	mJ
R_{thJC}				0.83 $^\circ\text{C/W}$
R_{thCK}			0.21	$^\circ\text{C/W}$

TO-247 (IXSH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		.242 BSC	

Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	